

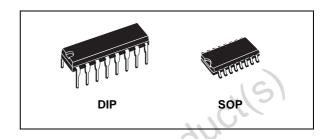
HCF4053B

TRIPLE 2-CHANNEL ANALOG MULTIPLEXER

- LOW "ON" RESISTANCE : 125Ω (Typ.) OVER 15V p.p SIGNAL-INPUT RANGE FOR V_{DD} - V_{EE} = 15V
- HIGH "OFF" RESISTANCE : CHANNEL LEAKAGE ± 100pA (Typ.) at V_{DD} V_{EE} = 18V
- BINARY ADDRESS DECODING ON CHIP
- HIGH DEGREE OF LINEARITY : < 0.5% DISTORTION TYP. at f_{IS} = 1KHz, V_{IS} = 5 V_{pp} , V_{DD} V_{SS} ≥ 10V, RL = 10K Ω
- VERY LOW QUIESCENT POWER DISSIPATION UNDER ALL DIGITAL CONTROL INPUT AND SUPPLY CONDITIONS: 0.2 µW (Typ.) at V_{DD} V_{SS} = V_{DD} V_{EE} =10V
- MATCHED SWITCH CHARACTERISTICS : $R_{ON} = 5Ω$ (Typ.) FOR V_{DD} $V_{EE} = 15V$
- WIDE RANGE OF DIGITAL AND ANALOG SIGNAL LEVELS: DIGITAL 3 to 20, ANALOG TO 20V p.p.
- QUIESCENT CURRENT SPECIF. UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

The HCF4053B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor



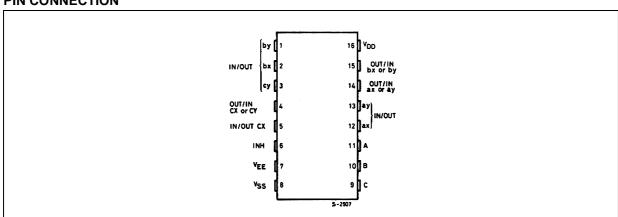
ORDER CODES

PACKAGE	TUBE	T&R
DIP	HCF4053BEY	
SOP	HCF4053BM1	HCF4053M013TR

technology available in DIP and SOP packages. The HCF4053B analog multiplexer/demultiplexer is a digitally controlled analog switch having low ON impedance and very low OFF leakage current. This multiplexer circuit dissipate extremely low quiescent power over the full $\rm V_{DD}$ - $\rm V_{SS}$ and $\rm V_{DD}$ - $\rm V_{EE}$ supply voltage range, independent of the logic state of the control signals.

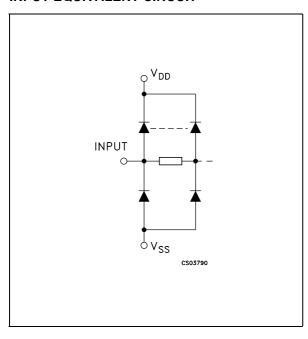
When a logic "1" is present at the inhibit input terminal all channel are off. This device is a triple 2-channel multiplexer having three separate digital control inputs, A, B, and C, and an inhibit input. Each control input selects one of a pair of channels which are connected in a single pole double-throw configuration.

PIN CONNECTION



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INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

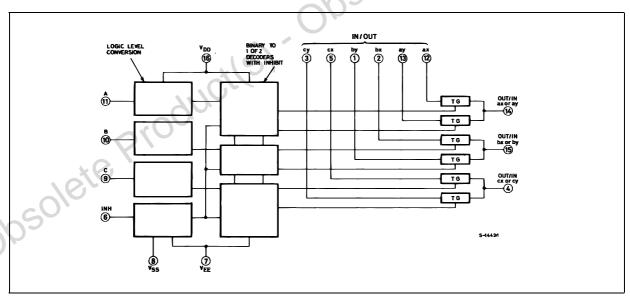
PIN No	SYMBOL	NAME AND FUNCTION						
11, 10, 9	A, B, C	Binary Control Inputs						
6	INH	Inhibit Inputs						
12, 13, 2, 1, 5, 3	IN/OUT	ax,ay,bx,by,cx,cy Input/ Output						
14	OUT/IN	ax or ay						
15	OUT/IN	bx or by						
4	OUT/IN	cx or cy						
7	V_{EE}	Supply Voltage						
8	V_{SS}	Negative Supply Voltage						
16	V_{DD}	Positive Supply Voltage						
TRUTH TABLE								
INHIBIT (or B or A	70,						

TRUTH TABLE

INHIBIT	C or B or A	00,
0	0	ax or bx or cx
0	. 01	ay or by or cy
1	X	NONE

X : Don't Care

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +22	V
VI	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
l _l	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	500 (*)	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value
V_{DD}	Supply Voltage	3 to 20
V _I	Input Voltage	0 to V _{DD}
T _{op}	Operating Temperature	-55 to 125
	-duct(s)	
	ate Product(s)	

DC SPECIFICATIONS

		T	est Cor	ndition					Value				Unit
Symbol	Parameter	V _{IS}	V _{EE}	V _{SS}	V _{DD}	Т	A = 25°	С	-40 to	85°C	-55 to	125°C	
		(V)	(V)	(V)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Device				5		0.04	5		150		150	
	Current (all				10		0.04	10		300		300	μA
	switches ON or all switches OFF)				15		0.04	20		600		600	μΑ
	Switches Of 1)				20		0.08	100		3000		3000	
SWITCH													
R _{ON}	Resistance	0 <u><</u> V _I <u><</u>			5		470	1050		1200		1200	
		V _{DD}	0	0	10		180	400		520		520	Ω
		• 00			15		125	280		360		360	
Δ_{ON}	Resistance Δ_{RON}	0 <u><</u> V _I <u><</u>			5		10				10		
	(between any 2 of	V _{DD}	0	0	10		10				5		Ω
	4 switches)	• 00			15		5				•		
OFF*	Channel Leakage Current (All Channel OFF) (COMMON O/I)		0	0	18		±0.1	100	6/	1000		1000	nA
OFF*	Channel Leakage Current (Any Channel OFF)		0	0	18	<u> </u>	±0.1	100		1000		1000	nA
C _I	Input Capacitance					Y	5						
Co	Output Capacitance		-5	-5	5		9						pF
C _{IO}	Feed through		(61			0.2						
CONTRO	DL (Address or Inhil	bit)	11:										l.
V _{IL}	Input Low Voltage	71)	Vee =	= V _{SS}	5			1.5		1.5		1.5	
		(O)		1KΩ	10			3		3		3	V
	210	= VDD thru	to \		15			4		4		4	
V _{IH}	Input High Voltage	triru 1KΩ	I _{IS} <	2μΑ	5	3.5			3.5		3.5		
	×6,			IOFF	10	7			7		7		V
	0,1		chan	nels)	15	11			11		11		
I _{IH} , I _L	Input Leakage Current	VI	= 0/18\	/	18		±10 ⁻³	±0.1		±1		±1	μΑ
Cı	Input Capacitance						5	7.5					pF

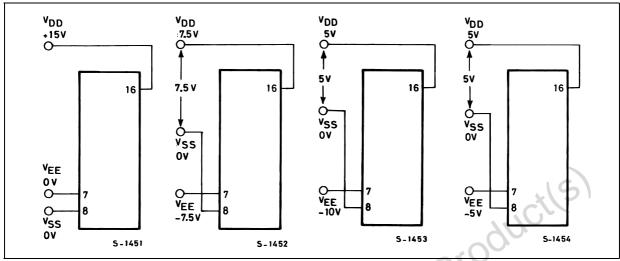
^{*} Determined by minimum feasible leakage measurement for automating testing.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_{L} = 50 pF$, all input square wave rise and fall time = 20 ns)

				Test Co	ndition				Value		Unit
Parameter	V _{EE} (V)	R _L (ΚΩ)	f _I (KHz)	V _I (V)	V _{SS} (V)	V _{DD} (V)		Min.	Тур.	Max.	
Propagation Delay				V		5			30	60	
Time (signal input to		200		V _{DD}		10			15	30	ns
output)						15			11	20	
Frequency Response Channel "ON" (sine wave input) at	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		25		MHz
20 log V _O /V _I = - 3dB				,			V _O at any channel		60	S	
Feed through (all channels OFF) at	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		10		MHz
$20 \log V_O/V_I = -40 dB$	- * \$\$	'		3()		10	V _O at any channel	0	8		IVII IZ
Frequency Signal Crosstalk at	= V _{SS}	1		5 <i>(</i> *)		10	Between any 2 Sections (IN pin 2, OUT pin 14)		2.5		MHz
$20 \log V_O/V_I = -40 dB$	- v SS	'		5(*)		0/9	Between any 2 Sections (IN pin 15, OUT pin 14)		6		IVITIZ
Cina Maya Diatartian				2(*)	-10:	5			0.3		
Sine Wave Distortion $f_{IS} = 1$ KHz Sine Wave	$=V_{SS}$	10	1	3(*)) \	10]		0.2		%
115 - 114 12 0 110 11410				5(*)		15			0.12		
CONTROL (Address	or Inhibi	t)									
Propagation Delay:	0		7/3	1	0	5			360	720	
Address to Signal	0	(0	10			160	320	ns
OUT (Channels ON or OFF)	0	ADD			0	15			120	240	113
0. 011)	-5	O			0	5			225	450	
Propagation Delay:	0				0	5			360	720	
Inhibit to Signal OUT	0	1			0	10			160	320	ns
(Channel turning ON)	0	'			0	15			120	240	113
10,0	-10				0	5			200	400	
Propagation Delay:	0					5			200	450	
Inhibit to Signal OUT	0	10				10			90	210	
(Channel turning OFF)	0	10				15]		70	160	ns
	-10					5]		130	300	
Address or Inhibit to Signal Crosstalk	0	10 ⁽¹⁾			0	10	$V_C = V_{DD} - V_{SS}$ (square wave)		65		mV peak

⁽¹⁾ Both ends of channel. * Peak to Peak voltage symmetrical about (V_{DD} - V_{EE}) /2

TYPICAL BIAS VOLTAGES



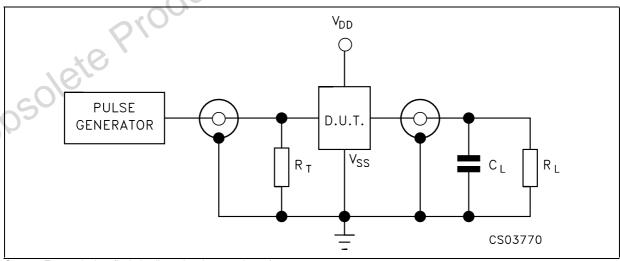
The ADDRESS (digital-control inputs) and INHIBIT logic levels are: "0"=V_{SS} and "1"=V_{DD}. The analog signal (through the TG) may swing from V_{EE} to V_{DD}

SPECIAL CONSIDERATIONS

Control of analog signals up to 20V peak to peak can be achieved by digital signal amplitudes of 4.5 to 20V (if V_{DD} - V_{SS} = 3V, a V_{DD} - V_{EE} of up to 13V can be controlled; for V_{DD} - V_{EE} level differences above 13V, a V_{DD} - V_{SS} of at least 4.5V is required. For example, if V_{DD} = +5, V_{SS} = 0, and V_{EE} = -13.5, analog signals from -13.5V to 4.5V can be controlled by digital inputs of 0 to 4.5V. In

certain applications, the external load resistor current may include both $\rm V_{\rm DD}$ and signal-line components. To avoid drawing $\rm V_{\rm DD}$ current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0,8V (calculated from RON values shown in DC SPECIFICATIONS). No V_{DD} current will flow through R_L if the switch current flows into leads 4, 14 and 15.

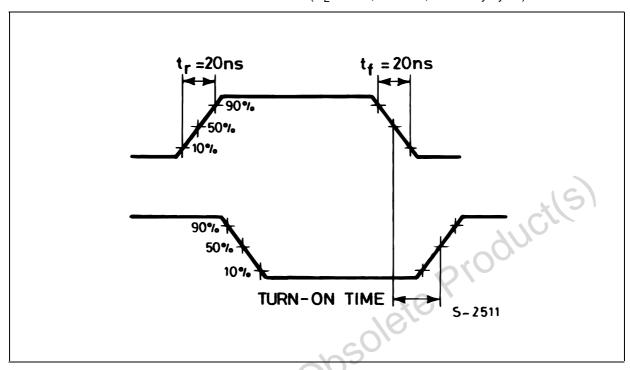
TEST CIRCUIT



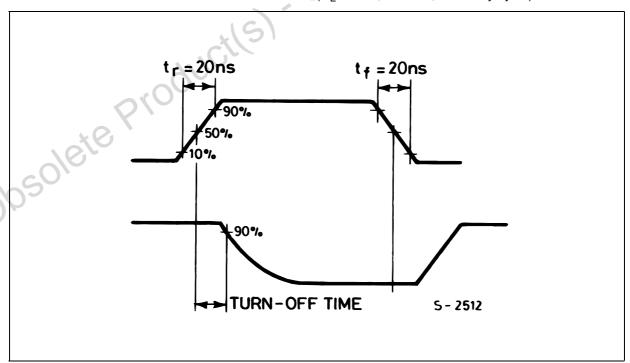
C_L = 50pF or equivalent (includes jig and probe capacitance)

 $R_L = 200 \text{K}\Omega$ $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM 1 : CHANNEL BEING TURNED ON ($R_L = 1K\Omega$, f=1MHz; 50% duty cycle)

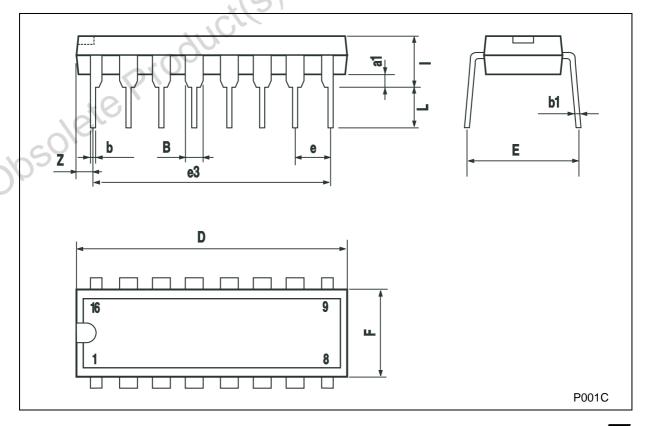


WAVEFORM 2 : CHANNEL BEING TURNED OFF ($R_L = 1K\Omega$, f=1MHz; 50% duty cycle)



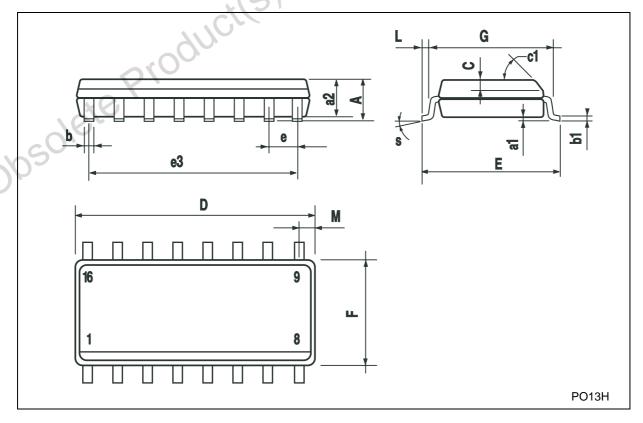
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN. TYP		MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010	16		
D			20		.(0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78		40,	0.700			
F			7.1	16/2		0.280		
I			5.1	0,		0.201		
L		3.3	Oh		0.130			
Z			1.27			0.050		



SO-16 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	.151
c1			45° (typ.)	.(
D	9.8		10	0.385	YO.	0.393
E	5.8		6.2	0.228	100	0.244
е		1.27			0.050	
e3		8.89		88	0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S			8° (m	nax.)		





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